

SANYO

No.4749

2SJ276P-Channel MOS Silicon FET
Very High-Speed
Switching Applications**Features**

- Low ON resistance.
- Very high-speed switching.
- Low-voltage drive.
- Surface mount type device making the following possible.
 - Reduction in the assembling time for 2SJ276-applied equipment.
 - High-density surface mount applications.
 - Small size of 2SJ276-applied equipment.

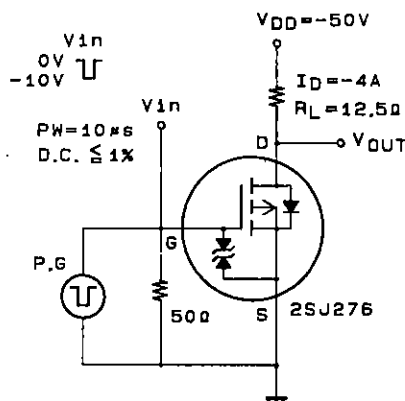
Absolute Maximum Ratings at $T_a = 25^\circ\text{C}$

			unit
Drain-to-Source Voltage	V_{DS}	-100	V
Gate-to-Source Voltage	V_{GS}	± 20	V
Drain Current (DC)	I_D	-8	A
Drain Current (Pulse)	I_{DP}	$PW \leq 10\mu s, \text{ duty cycle} \leq 1\%$	A
Allowable Power Dissipation	P_D	1.65	W
		$T_c = 25^\circ\text{C}$	60
Channel Temperature	T_{ch}	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

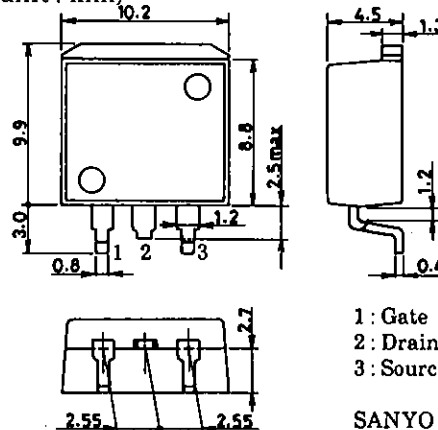
Electrical Characteristics at $T_a = 25^\circ\text{C}$

			min	typ	max	unit
D-S Breakdown Voltage	$V_{(BR)DSS}$	$I_D = -1\text{mA}, V_{GS} = 0$	-100			V
G-S Breakdown Voltage	$V_{(BR)GSS}$	$I_G = \pm 100\mu A, V_{DS} = 0$	± 20			V
Zero-Gate Voltage	I_{DSS}	$V_{DS} = -100\text{V}, V_{GS} = 0$			-100	μA
Drain Current						
Gate-to-Source Leakage Current	I_{GSS}	$V_{GS} = \pm 16\text{V}, V_{DS} = 0$			± 10	μA
Gate-to-Source Cutoff Voltage	$V_{GS(off)}$	$V_{DS} = -10\text{V}, I_D = -1\text{mA}$	-1.0		-2.0	V
Forward Transfer Admittance	$ Y_{fs} $	$V_{DS} = -10\text{V}, I_D = -4\text{A}$	3.5	6.5		S
Static Drain-to-Source	$R_{DS(on)}$	$I_D = -4\text{A}, V_{GS} = -10\text{V}$		0.22	0.3	Ω
ON-State Resistance	$R_{DS(on)}$	$I_D = -4\text{A}, V_{GS} = -4\text{V}$		0.3	0.4	Ω

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Switching Time Test Circuit**Package Dimensions 2090A**

(unit: mm)

1: Gate
2: Drain
3: Source

SANYO: SMP-FD

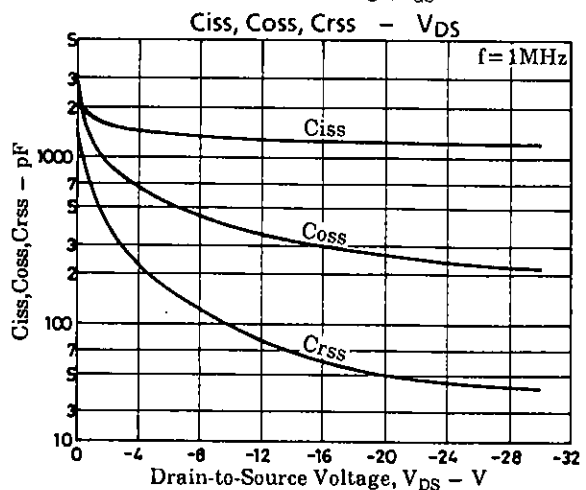
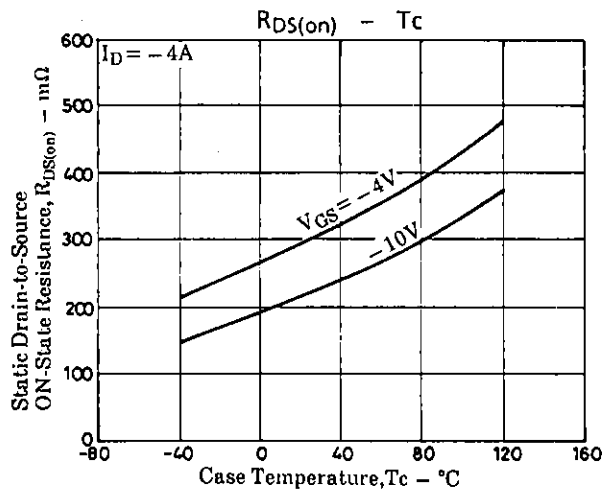
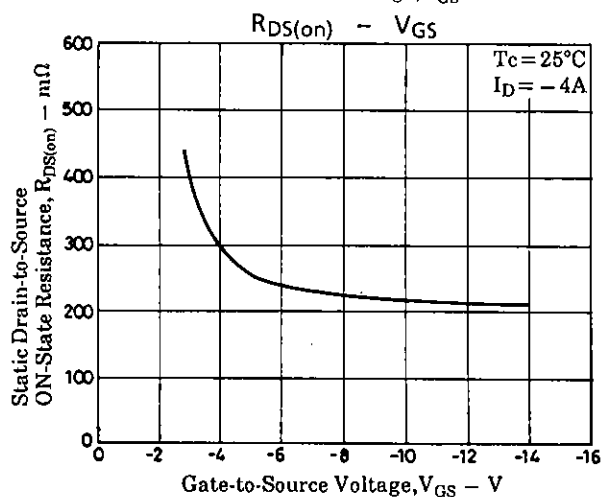
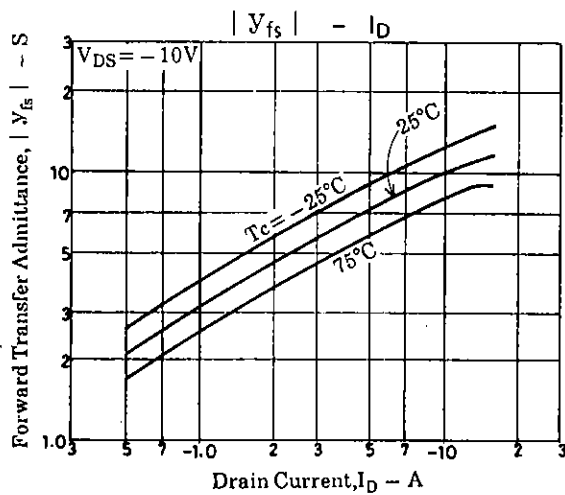
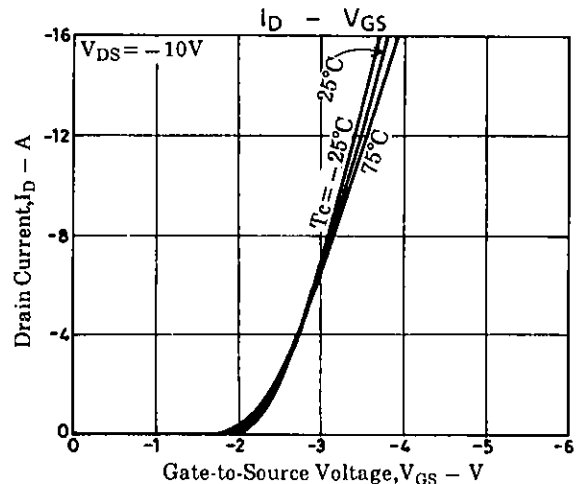
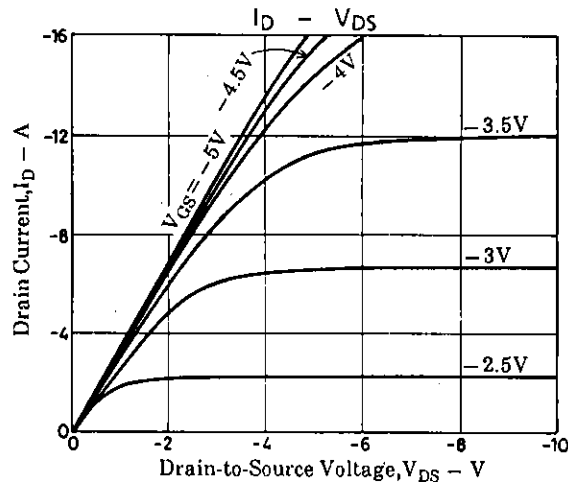
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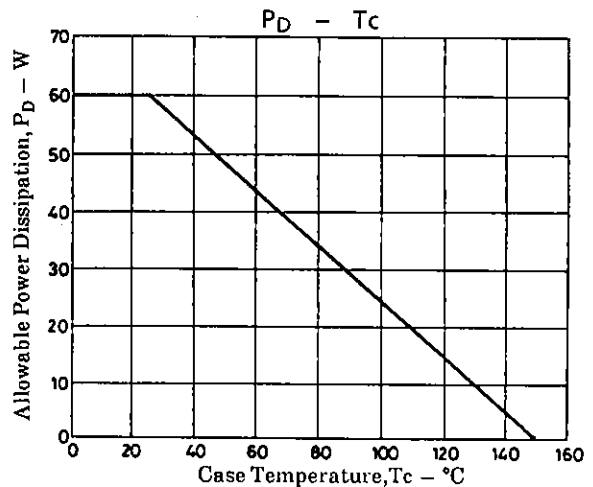
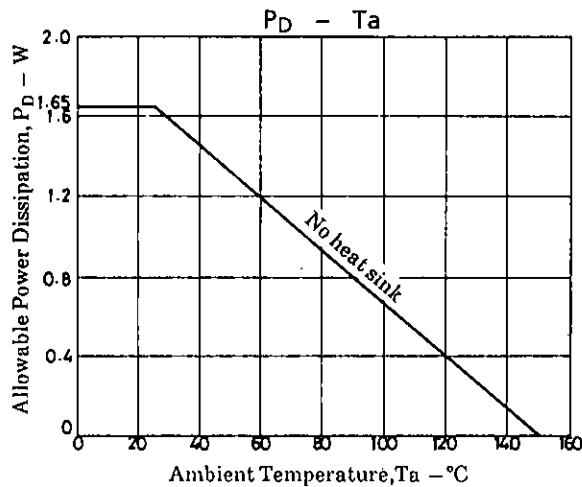
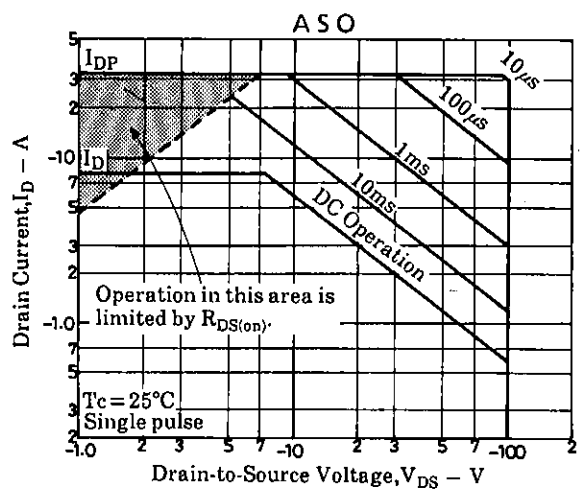
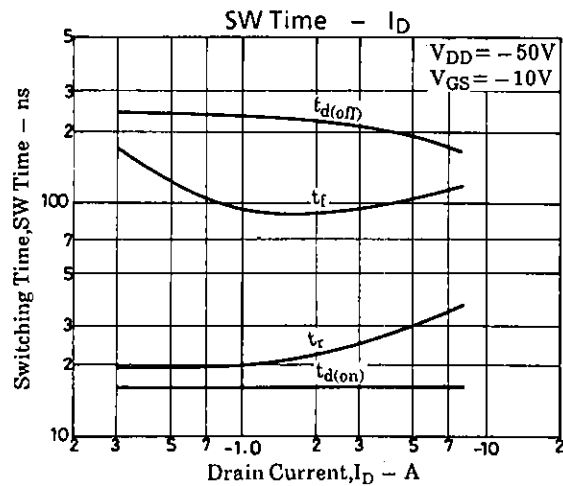
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11195TS (KOTO) BX-1179 No.4749-1/3

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			min	typ	max	unit
Input Capacitance	C_{iss}	$V_{DS} = -20V, f = 1MHz$		1230		pF
Output Capacitance	C_{oss}	$V_{DS} = -20V, f = 1MHz$		260		pF
Reverse Transfer Capacitance	C_{rss}	$V_{DS} = -20V, f = 1MHz$		50		pF
Turn-ON Delay Time	$t_{d(on)}$	See specified Test Circuit.		16		ns
Rise Time	t_r	"		27		ns
Turn-OFF Delay Time	$t_{d(off)}$	"		200		ns
Fall Time	t_f	"		100		ns
Diode Forward Voltage	V_{SD}	$I_S = -8A, V_{GS} = 0$	-1.0	-1.5		V





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